

TECHNICAL DATA DATA SHEET 885, REV. C

SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings⁽¹⁾:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	- 150		V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular 15 wave form 280		Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	280	Α
Max. Junction Temperature	T _J	65 to +200		°C
Max. Storage Temperature	T _{stq}	-	-65 to +200	°C

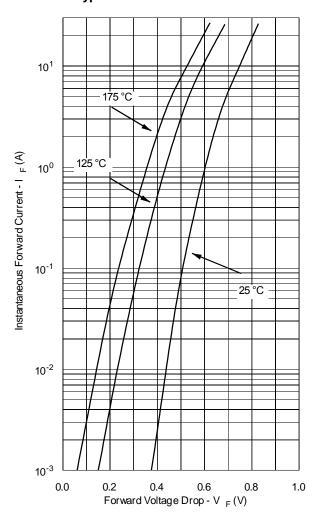
Electrical Characteristics(1):

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 15A, Pulse, T _J = 25 °C	0.89	V
	V_{F2}	@ 15A, Pulse, T _J = 125 °C	0.74	V
Max. Reverse Current	I _{R1}	@V _R = 150V, Pulse,	500	μΑ
		T _J = 25 °C		·
	I _{R2}	@V _R = 150V, Pulse,	8	mA
		T _J = 125 °C		
Max. Junction Capacitance	C _T	$@V_R = 5V, T_C = 25 ^{\circ}C$	500	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV} \text{ (p-p)}$		

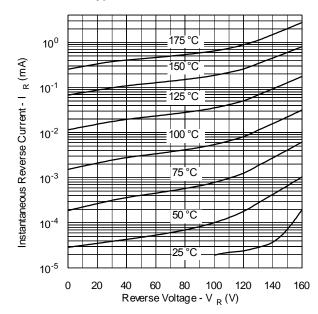
(1) in SHD package

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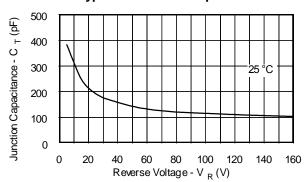
Typical Forward Characteristics



Typical Reverse Characteristics

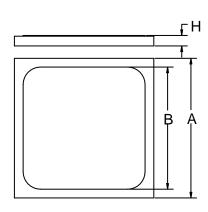


Typical Junction Capacitance



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Mechanical Dimensions: In Inches / mm



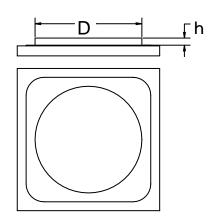


Figure 1 Figure 2

A	В	D	H	h
0.125±0.003	0.116±0.003	0.070±0.005	0.0155±0.001 B version 0.0105±0.001 A version	0.010±0.002

Top side (Anode) metallization:

A = AI - 25 kÅ, Figure 1

B = Ag - 30 kÅ, Figure 1

C = With gold plated moly disc on the top, Figure 2

Bottom side (Cathode) metallization: A, B, C = Ti/Ni/Ag - 5 kÅ minimum.

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